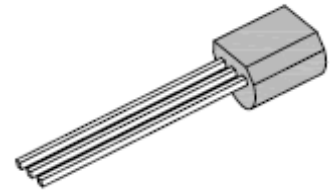


Small Signal High Voltage Transistor (NPN)

Features

- High Voltage NPN Transistor for General Purpose and Telephony Applications



Mechanical Data

Case:	TO-92, Plastic Package
Terminals:	Solderable per MIL-STD-202G, Method 208
Weight:	0.18 gram

TO-92



Maximum Ratings *(T_{Ambient}=25°C unless noted otherwise)*

Symbol	Description	2N5551	Unit	Conditions
V_{CBO}	Collector-Base Voltage	180	V	
V_{CEO}	Collector-Emitter Voltage	160	V	
V_{EBO}	Emitter-Base Voltage	6.0	V	
I_c	Collector Current Continuous	600	mA	
P_D	Power Dissipation at T _a =25°C	625	mW	Measured with the device soldered into a typical printed circuit board
	Derate above 25°C	5.0	mW/°C	
R_{θJC}	Junction to Case	125	°C/W	Measured with the device soldered into a typical printed circuit board
R_{θJA}	Junction to Ambient	357		
T_J, T_{STG}	Operation and Storage Junction Temperature Range	-55 to +150	°C	

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Electrical Characteristics ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	Min.	Max.	Unit	Conditions
hFE*	D.C. Current Gain	80	-		VCE=5V, IC=1mA
		80	400		VCE=5V, IC=10mA
		50	-		VCE=5V, IC=50mA
ICBO	Collector Cut-Off Current	-	50	nA	VCB=120V, IE=0
IEBO	Emitter Cut-Off Current	-	50	nA	VEB=4V, IC=0
VCE(Sat)*	Collector Emitter Saturation Voltage	-	0.15	V	IC=10mA, IB=1mA
		-	0.2		IC=50mA, IB=5mA
VBE(Sat)*	Base Emitter Saturation Voltage	-	1.0	V	IC=10mA, IB=1mA
			1.0		IC=50mA, IB=5mA
VCBO	Collector-Base Voltage	180	-	V	IC=100μA, IE=0
VCEO	Collector-Emitter Voltage	160	-	V	IC=1mA, IB=0
VEBO	Emitter-Base Voltage	6.0	-	V	IE=10μA, IC=0
ft	Transition Frequency	100	300	MHz	VCE=10V, IC=10mA, f=100MHz
Cob	Output Capacitance	-	6.0	pF	VCB=10V, f=1.0MHz, IE=0

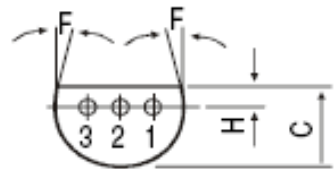
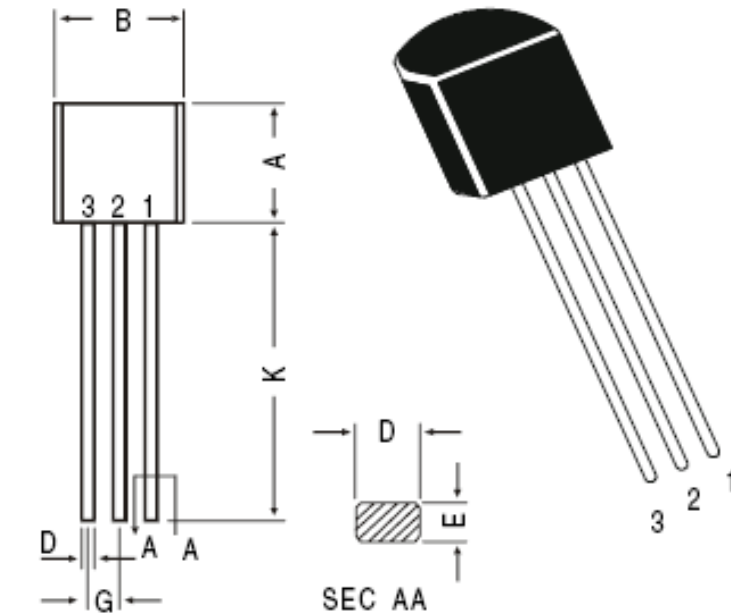
*Pulse Test: Pulse Width=300μs, Duty Cycle=2%

Small Signal High Voltage Transistor (NPN)

2N5551

Dimensions in mm

TO-92



PIN CONFIGURATION
 1. COLLECTOR
 2. BASE
 3. EMITTER

All dimensions in mm.

DIM	MIN.	MAX.
A	4.33	4.83
B	4.33	4.83
C	3.36	3.76
D	0.36	0.56
E	0.36	0.56
F	5 DEG	
G	1.14	1.40
H	1.14	1.53
K	12.70	—

Small Signal High Voltage Transistor (NPN)

2N5551

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